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A systematic analysis of defects in ion-implanted silicon

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#	Paper	IF	Citations
466	Modulated optical reflectance measurements on amorphous silicon layers and detection of residual defects. <i>Applied Physics A: Solids and Surfaces</i> , 1988 , 47, 147-155		33
465	Lattice Defects in High-Dose As Implantation into Localized Si Area. <i>Japanese Journal of Applied Physics</i> , 1988 , 27, 2209-2217	1.4	21
464	The Effect of Implant Species on the Stability of Ion Implantation Damage. 1988 , 100, 277		7
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